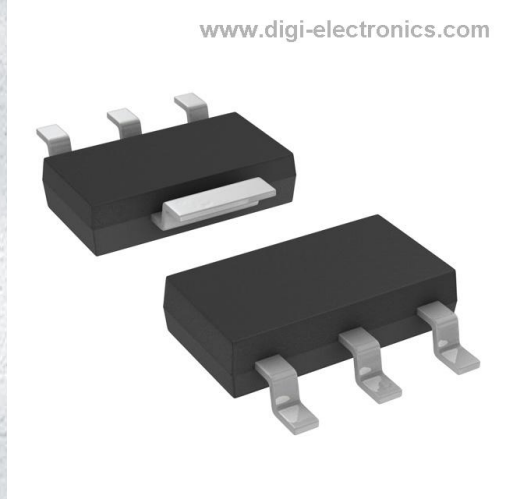
CPC5602CTR Datasheet



DiGi Electronics Part Number	CPC5602CTR-DG
Manufacturer	IXYS Integrated Circuits Division
Manufacturer Product Number	CPC5602CTR
Description	MOSFET N-CH 350V 5MA SOT-223
Detailed Description	N-Channel 350 V 5mA (Ta) 2.5W (Ta) Surface Mount SOT-223

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

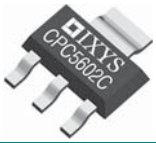
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
CPC5602CTR	IXYS Integrated Circuits Division
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
350 V	5mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
0.35V	14Ohm @ 50mA, 350mV
Vgs(th) (Max) @ Id:	Vgs (Max):
-	±20V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
300 pF @ 0 V	Depletion Mode
Power Dissipation (Max):	Operating Temperature:
2.5W (Ta)	-40°C ~ 85°C (TA)
Mounting Type:	Supplier Device Package:
Surface Mount	SOT-223
Package / Case:	Base Product Number:
TO-261-4, TO-261AA	CPC5602

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

IXYS
INTEGRATED CIRCUITS DIVISION



CPC5602
N-Channel Depletion Mode FET

Parameter	Rating	Units
Drain-to-Source Voltage - V_{DS}	350	V
Max On-Resistance - $R_{DS(on)}$	14	Ω
Max Power	2.5	W

Features

- 350V Drain-to-Source Voltage
- Depletion Mode Device Offers Low $R_{DS(on)}$ at Cold Temperatures
- Low On-resistance: 8Ω (Typical) @ 25°C
- Low $V_{GS(off)}$ Voltage: -2.0V to -3.6V
- High Input Impedance
- Low Input and Output Leakage
- Small Package Size SOT-223
- PC Card (PCMCIA) Compatible
- PCB Space and Cost Savings

Applications

- Support Component for LITELINK™ Data Access Arrangement (DAA)
- Telecommunications
- Normally On Switches
- Ignition Modules
- Converters
- Security
- Power Supplies

Description

The CPC5602 is an N-channel depletion mode Field Effect Transistor (FET) that utilizes IXYS Integrated Circuits Division's proprietary third generation vertical DMOS process. The third generation process realizes world class, high voltage MOSFET performance in an economical silicon gate process. The vertical DMOS process yields a highly reliable device, particularly in difficult application environments such as telecommunications, security, and power supplies.

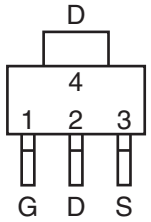
One of the primary applications for the CPC5602 is as a linear regulator/hook switch for the LITELINK family of Data Access Arrangements (DAA) Devices CPC5620A, CPC5621A, and CPC5622A.

The CPC5602 has a typical on-resistance of 8Ω, a drain-to-source voltage of 350V, and is available in an SOT-223 package. As with all MOS devices, the FET structure prevents thermal runaway and thermal-induced secondary breakdown.

Ordering Information

Part #	Description
CPC5602CTR	N-Channel Depletion Mode FET, SOT-223 Pkg. Tape and Reel (1000/Reel)

Package Pinout



Pin Number	Name
1	GATE
2	DRAIN
3	SOURCE
4	DRAIN

Absolute Maximum Ratings @ 25ºC

Parameter	Symbol	Ratings	Units
Drain-to-Source Voltage	V_{DS}	350	V
Gate-to-Source Voltage	V_{GS}	±20	V
Total Package Dissipation	P	2.5	W
Operational Temperature	T_A	-40 to +85	ºC
Storage Temperature	T_A	-40 to +125	ºC

Absolute Maximum Ratings are stress ratings. Stresses in excess of these ratings can cause permanent damage to the device. Functional operation of the device at conditions beyond those indicated in the operational sections of this data sheet is not implied.

Electrical Characteristics @25ºC (Unless Otherwise Specified)

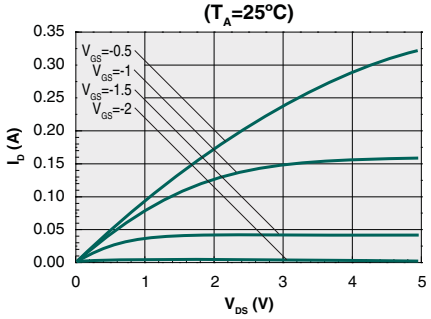
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Gate-to-Source Off Voltage	$V_{GS(off)}$	I_D= 2µA, V_{DS}=10V, V_{DS}=100V	-2	-2.62	-3.6	V
Drain-to-Source Leakage Current	$I_{DS(off)}$	V_{GS}= -5V, V_{DS}=190V	-	-	20	nA
		V_{GS}= -5V, V_{DS}=350V	-	-	1	µA
Drain Current	I_D	V_{GS}= -2.7V, V_{DS}=5V, V_{DS}=50V	-	-	5	mA
		V_{GS}= -0.57V, V_{DS}=5V	130	-	-	mA
On-Resistance	$R_{DS(on)}$	V_{GS}= -0.35V, I_{DS}=50mA	-	8	14	Ω
Gate Leakage Current	I_{GSS}	V_{GS}=10V, V_{GS}=-10V	-	-	0.1	µA
Gate Capacitance	C_{ISS}	V_{DS}= V_{GS}=0V	-	-	300	pF

Thermal Characteristics

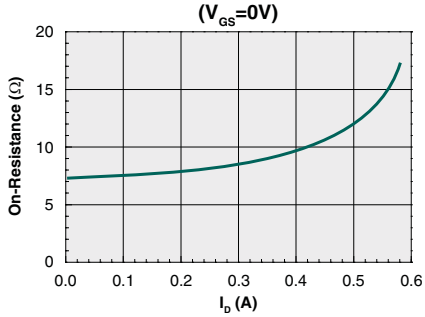
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Thermal Resistance	$R_{\theta JC}$	-	-	-	14	ºC/W

PERFORMANCE DATA*

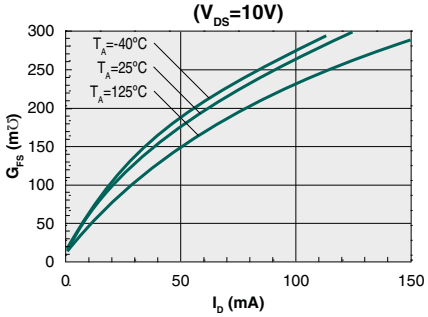
Output Characteristics (T_A=25°C)



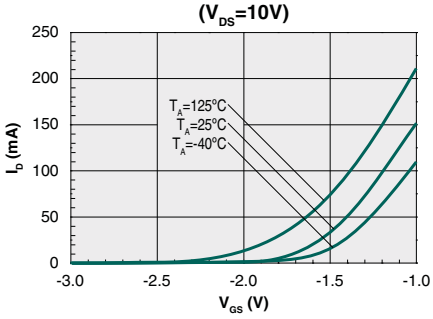
On-Resistance vs. Drain Current (V_{GS}=0V)



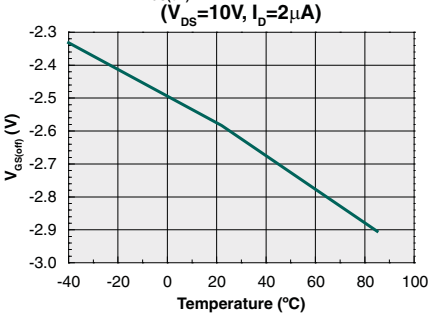
Transconductance vs Drain Current (V_{DS}=10V)



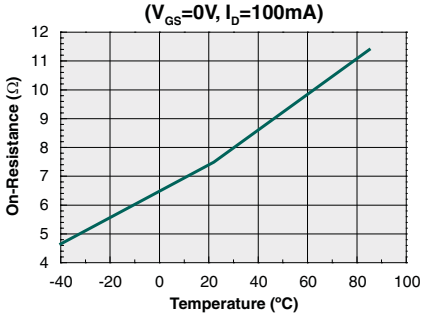
Transfer Characteristics (V_{DS}=10V)



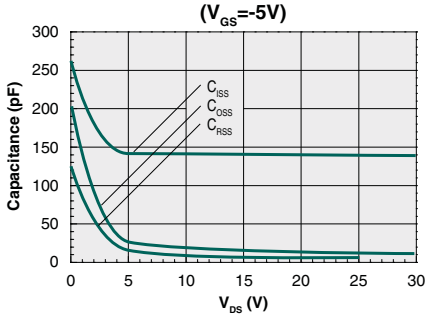
$V_{GS(off)}$ vs. Temperature (V_{DS}=10V, I_D=2μA)



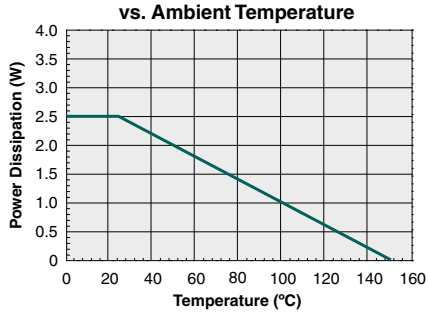
On-Resistance vs. Temperature (V_{GS}=0V, I_D=100mA)



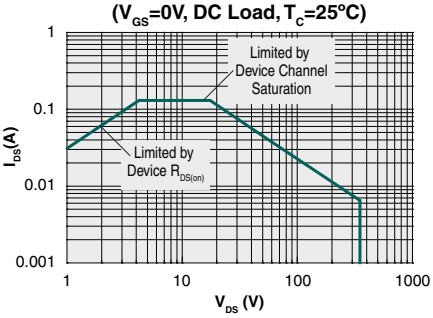
Capacitance vs. Drain-Source Voltage (V_{GS}=-5V)



Power Dissipation vs. Ambient Temperature



Forward Safe Operating Bias (V_{GS}=0V, DC Load, T_C=25°C)



*The Performance data shown in the graphs above is typical of device performance. For guaranteed parameters not indicated in the written specifications, please contact our application department.

Manufacturing Information

Moisture Sensitivity

All plastic encapsulated semiconductor packages are susceptible to moisture ingression. IXYS Integrated Circuits Division classified all of its plastic encapsulated devices for moisture sensitivity according to the latest version of the joint industry standard, **IPC/JEDEC J-STD-020**, in force at the time of product evaluation. We test all of our products to the maximum conditions set forth in the standard, and guarantee proper operation of our devices when handled according to the limitations and information in that standard as well as to any limitations set forth in the information or standards referenced below.

Failure to adhere to the warnings or limitations as established by the listed specifications could result in reduced product performance, reduction of operable life, and/or reduction of overall reliability.

This product carries a **Moisture Sensitivity Level (MSL) rating** as shown below, and should be handled according to the requirements of the latest version of the joint industry standard **IPC/JEDEC J-STD-033**.

Device	Moisture Sensitivity Level (MSL) Rating
CPC5602C	MSL 1

ESD Sensitivity

This product is **ESD Sensitive**, and should be handled according to the industry standard **JESD-625**.

Soldering Profile

This product has a maximum body temperature and time rating as shown below. All other guidelines of **J-STD-020** must be observed.

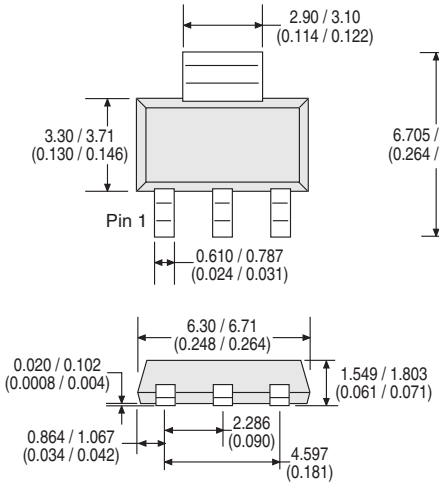
Device	Maximum Temperature x Time
CPC5602C	260°C for 30 seconds

Board Wash

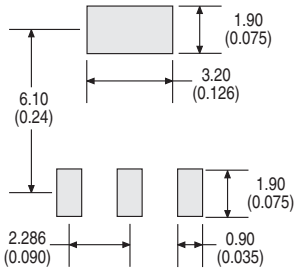
IXYS Integrated Circuits Division recommends the use of no-clean flux formulations. However, board washing to remove flux residue is acceptable, and the use of a short drying bake may be necessary. Chlorine-based or Fluorine-based solvents or fluxes should not be used. Cleaning methods that employ ultrasonic energy should not be used.

MECHANICAL DIMENSIONS

CPC5602C

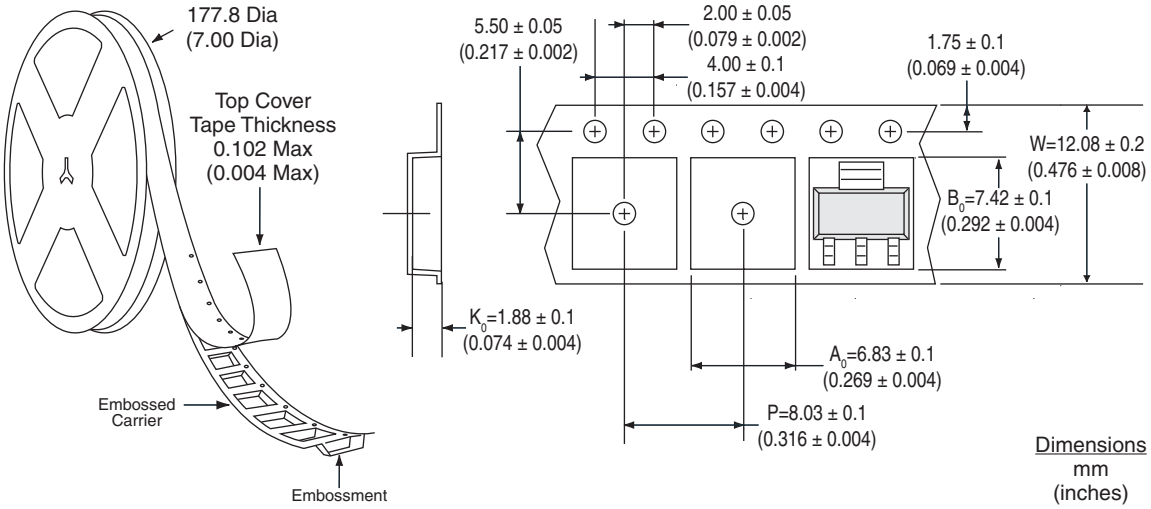


PCB Land Pattern



Dimensions
mm MIN / mm MAX
(inches MIN / inches MAX)

CPC5602CTR Tape & Reel



Dimensions
mm
(inches)

For additional information please visit our website at: www.ixysic.com

Specification: DS-CPC5602-R10

7/20/2015

The information below supercedes any previously presented material.

For additional information please visit our website at: https://www.littelfuse.com

IXYS
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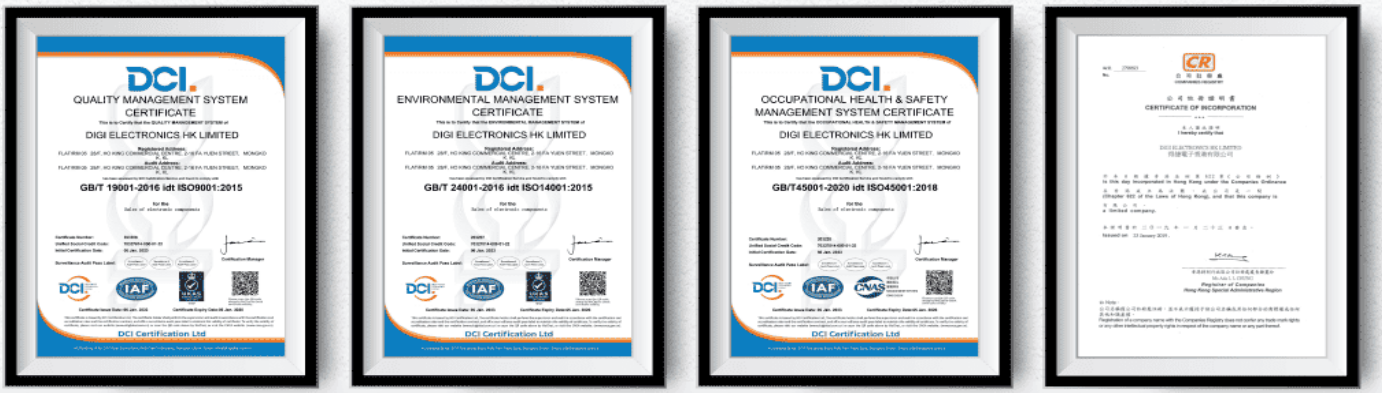

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